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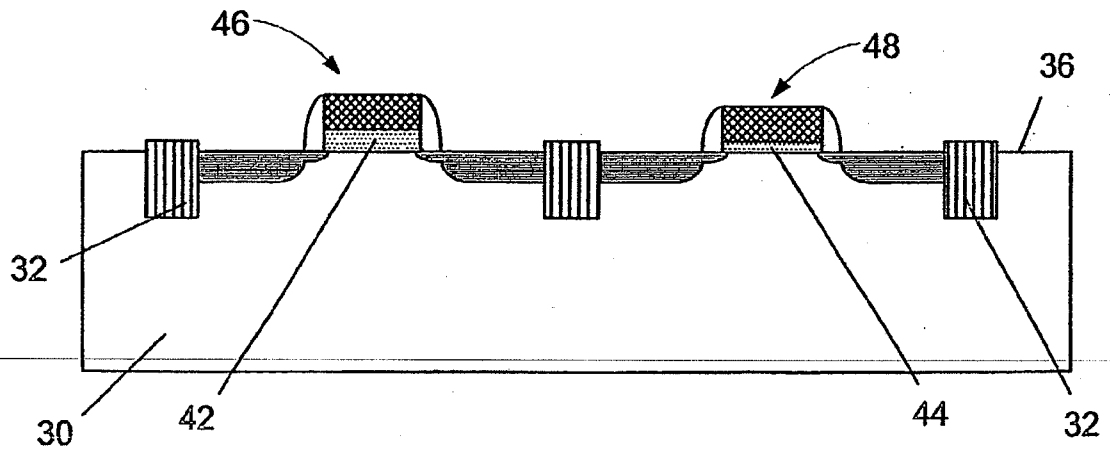
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(54) Title: METHOD OF MAKING TRANSISTORS WITH GATE INSULATION LAYERS OF DIFFERING THICKNESS



(57) Abstract: In one illustrative embodiment, the method comprises forming a sacrificial layer of material (34) above a substrate (30) comprised of silicon, performing a wet etching process to remove the sacrificial layer (34), implanting fluorine atoms into selected portions of the substrate (30) after the sacrificial layer (34) is removed, and performing a thermal oxidation process to form a plurality of gate insulation layers (42, 44) above the substrate (30), the gate insulation layers (42) formed above the fluorine implanted selected portions of the substrate (30) having a thickness that is greater than a thickness of the gate insulation layers (44) formed above portions of the substrate (30) not implanted with fluorine.

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